ADVANCED COMPONENTS PACKAGING

256 Megabit CMOS DDR SDRAM

DPDD64MX4TSAY5

DESCRIPTION:

The Memory Stack™ series is a family of interchangeable memory moduels. The 256 Megabit Double Data Rate Synchronous DRAM module is a member of this family which utilizes the space saving LP-Stack™ TSOP stacking technology. The devices are constructed with two 32 Meg x 4 DDR SDRAMs.

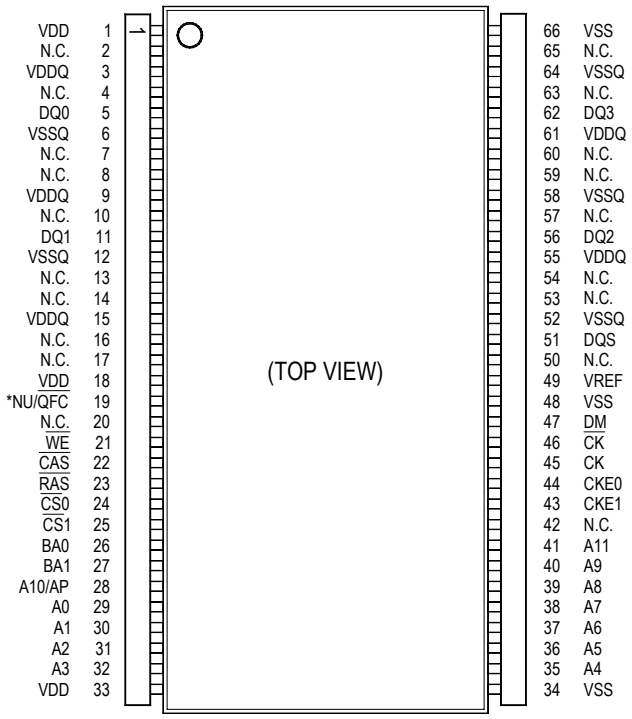
This 128 Megabit based LP-Stack™ module, DPDD64MX4TSAY5, has been designed to fit in the same footprint as the 32 Meg x 4 DDR SDRAM TSOP monolithic. This allows system upgrade without electrical or mechanical redesign, providing an immediate and low cost memory solution.

FEATURES:

- Configuration Available:
  64 Meg x 4 (2 Banks of 8 Meg x 4 bits x 4 banks)
- Clock Frequency: 100, 125, 133, 143, 167 MHz (max.)
- 2.5 Volt DQ Supply
- JEDEC Standard SSTL_2 Interface for all Inputs/Outputs
- Four Bank Operation
- Programmable Burst Type: Burst Length and Read Latency
- Refresh: 4096 Cycles/64ms
- Refresh Types: Auto and Self
- IPC-A-610 Manufacturing Standards
- JEDEC Approved Footprint and Pinout
- Package: 66-Pin Leaded TSOP Stack

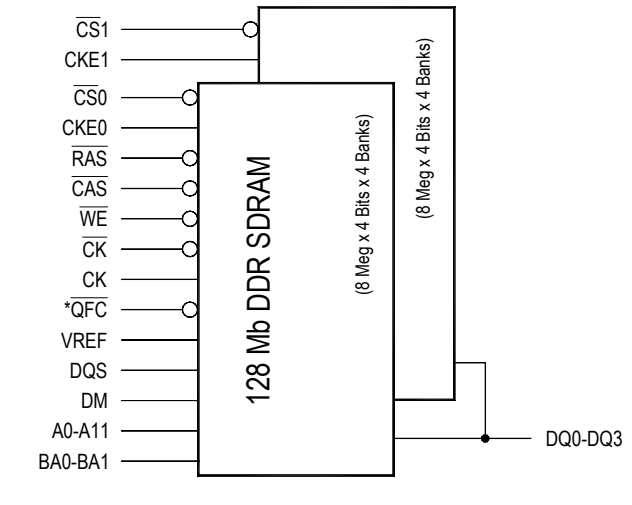
PIN NAMES	
A0-A11	Row Address: A0-A11 Column Address: A0-A9, A11
BA0,BA1	Bank Select Address
A10/AP	Auto Precharge
DQ0-DQ3	Data In/Data Out
$\overline{CAS}$	Column Address Strobe
$\overline{CS0}$, $\overline{CS1}$	Chip Selects
$\overline{RAS}$	Row Address Strobe
$\overline{WE}$	Data Write Enable
CK, $\overline{CK}$	Differential Clock Inputs
CKE0, CKE1	Clock Enables
DQS	Data Strobe
DM	Data Mask
$\overline{QFC}$	DQ FET Switch Control
VDD	Power Supply (+2.5V)
Vss	Ground
VDDQ	DQ Power Supply (+2.5V)
VssQ	DQ Ground
VREF	Reference Voltage for inputs
N.C.	No Connect
NU	Not Used, Electrical Connect is Present

PIN-OUT DIAGRAM



* This pin is a No Connect for some manufacturers.

FUNCTIONAL BLOCK DIAGRAM



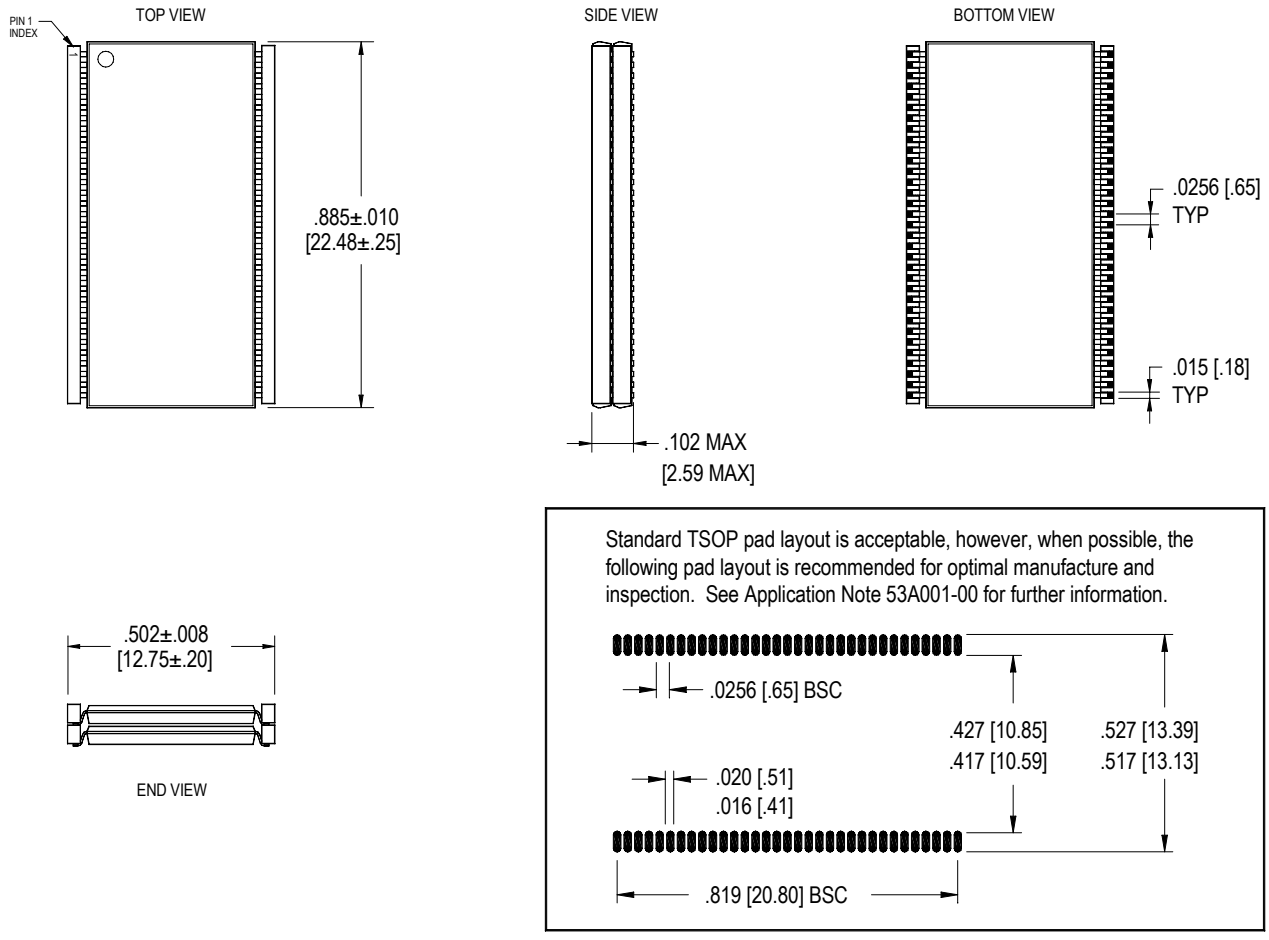
ORDERING INFORMATION

DP	DD	64M	X	4	T	S	A	Y5	-	DP	-	XX	XX	XX
PREFIX	TYPE	MEMORY DEPTH	DESIG	MEMORY WIDTH	DESIG	I/O TYPE	DEVICE WIDTH	PACKAGE		SUPPLIER		MFR ID	CYCLE TIME	CAS LATENCY

- CAS LATENCY: 15 = CAS LATENCY 1.5; 20 = CAS LATENCY 2.0; 25 = CAS LATENCY 2.5; 30 = CAS LATENCY 3.0
- CYCLE TIME: 60 = 6ns (166MHz); 70 = 7ns (143MHz); 75 = 7.5ns (133MHz); 08 = 8ns (125MHz); 10 = 10ns (100MHz)
- MFR ID: MANUFACTURER CODE *
- SUPPLIER: SUPPLIER CODE *
- PACKAGE: STACKABLE TSOP
- DEVICE WIDTH: x4 MEMORY BASED
- I/O TYPE: SSTL INPUTS/OUTPUTS
- DESIG: 128 MEGABIT BASED
- DESIG: MEMORY MODULE WITHOUT SUPPORT LOGIC
- TYPE: DOUBLE DATA RATE SYNCHRONOUS DRAM

* Contact your sales representative for supplier and manufacturer codes.

MECHANICAL DRAWING



Standard TSOP pad layout is acceptable, however, when possible, the following pad layout is recommended for optimal manufacture and inspection. See Application Note 53A001-00 for further information.

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